

CENTRAL FAX CENTER

OCT 19 2005

P910351

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of: Hsu et al.

U.S. Serial No: 10/627,000

Filed: July 25, 2003

For: METHOD FOR FORMING NON-
VOLATILE MEMORY CELL WITH
LOW-TEMPERATURE-FORMED
DIELECTRIC BETWEEN WORD AND
BIT LINES, AND NON-VOLATILE
MEMORY ARRAY INCLUDING SUCH
MEMORY CELLS

/ Examiner: Schillinger, Laura M.

/ Group Art: 2813

CERTIFICATE OF FACSIMILE TRANSMISSION

I hereby certify that this paper is being facsimile
transmitted to: Commissioner for Patents at fax number 571-
273-8300 on October 19, 2005.


Kenton R. Mullins, Reg. No. 36,331


TRANSMITTAL

Sir:

Submitted herewith are (6 pages including this Transmittal):

- (1) Amendment; and
- (2) Deposit Account Authorization: The Commissioner is hereby authorized to charge any needed fees to deposit account 50-1600.

Respectfully submitted,


Kenton R. Mullins
Attorney for Applicants
Registration No. 36,331

October 19, 2005
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Kenton R. Mullins, Reg. No. 36,331**AMENDMENT**

Dear Sir:

In further response to the Office Action mailed July 20, 2005 and the Advisory Action, Applicants respectfully request that the following amendment be entered in the above-identified patent application:

Listing of the Claims are reflected in the listing of claims, which begins on page 2 of this paper.

Remarks/Arguments begin on page 5 of this paper.